

File Number 1530

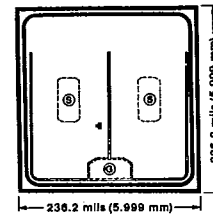
PCF35N08

N-Channel Enhancement-Mode Power Field-Effect Transistor Chip

80 V, 35 A, 0.055 Ω

Features:

- **Contact metallization:**
Gate and source-aluminum
Drain-tri-metal (Al-Ti-Ni)
- **Assembly recommendations:**
Gate and source-10-mil aluminum wire
Drain-mounted with 95/5 lead-tin solder
- Die Number-09288
- Device types that are derived
from PCF35N08-
RFK35N08
RFK35N10



ATTACH AREAS:
 ⓐ Source 0.060" x 0.030" (1.524 mm x 0.762 mm)
 ⓑ Gate 0.030" x 0.060" (0.762 mm x 1.524 mm)
 ⓓ Back Side - Drain
 DIE THICKNESS - 14 ± 1 mils (0.356 ± 0.025 mm)

CHIP LAYOUT

Electrical Characteristics at 25°C

The chip is 100% probed to the actual conditions and limits specified.

Characteristic	Test Conditions	Limits		Units
		PCF35N08		
		Min.	Max.	
V_{DSS}	$I_D=1 \text{ mA}$ $V_{GS}=0$	80	—	V
$V_{GS(th)}$	$V_{GS}=V_{DS}$ $I_D=1 \text{ mA}$	2	4	V
I_{DSS}	$V_{DS}=65 \text{ V}$	—	1	μA
I_{CS}	$V_{GS}=\pm 20 \text{ V}$ $V_{DS}=0$	—	100	nA
$V_{GS} \text{ (ON)}^a$	$I_D=17.5 \text{ A}$ $V_{GS}=10 \text{ V}$	—	0.963	V
g_{fs}^a	$V_{DS}=10 \text{ V}$ $I_D=17.5 \text{ A}$	10	—	mho

^aPulsed; pulse duration=300 μs max., duty factor = 2%